

UNISONIC TECHNOLOGIES CO., LTD

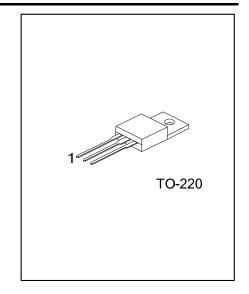
UTF1404 **Preliminary Power MOSFET**

160A, 40V N-CHANNEL **POWER MOSFET**

DESCRIPTION

The UTC UTF1404 is an N-channel enhancement MOSFET, it uses UTC's advanced technology to provide the customers with perfect R_{DS(ON)} and high switching speed.

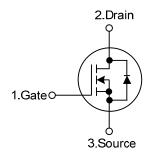
The UTC UTF1404 is suitable for all commercial-industrial applications at power dissipation levels to approximately 50 watts,



FEATURES

- * $R_{DS(ON)}$ =3.5m Ω @ V_{GS} =10V, I_D =95A
- * High Switching Speed

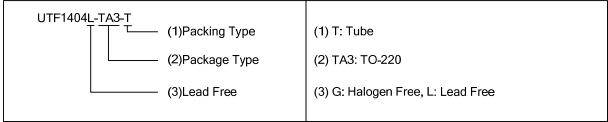
SYMBOL



ORDERING INFORMATION

Ordering Number		Dealeana	Pin	Assignme	Dealing		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTF1404L-TA3-T	UTF1404G-TA3-T	TO-220	G	D	S	Tube	

Pin Assignment: G: Gate D: Drain S: Source Note:



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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER				SYMBOL	RATINGS	UNIT
Drain-Source Voltage				V_{DSS}	40	V
Gate-Source Voltage				V_{GSS}	±20	V
Drain Current	Continu	Continuous (V_{GS} =10V) $\frac{T_{G}}{T_{G}}$		- I _D	162 (Note 4)	Α
	Continu				115 (Note 4)	Α
	Pulsed (Pulsed (Note 2)		I _{DM}	650	Α
Avalanche Curr	Avalanche Current (Note 2)		I _{AR}	95	Α	
Single Pulsed (Note 3)		(Note 3)	E _{AS}	519	mJ	
Avalanche Ene	rgy	Repetitive (Note 2)		E _{AR}	±20 V 162 (Note 4) A 115 (Note 4) A 650 A 95 A 519 m 20 m 166 V +150 °C	mJ
Power Dissipation (T _C =25°C)		on (T _C =25°C)		P_D	166	W
Junction Temperature		T_J	+150	°C		
Storage Temperature			nperature		-55~+150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive rating: pulse width limited by maximum junction temperature
- 3. Starting T_J =25°C, L=0.12mH, R_G =25 Ω , I_{AS} =95A
- 4. Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62	°C/W
Junction to Case	θıc	0.75	°C/W

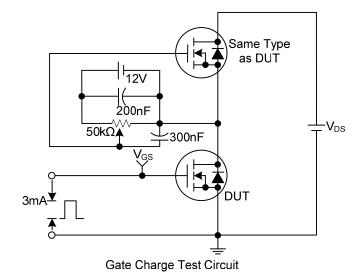
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

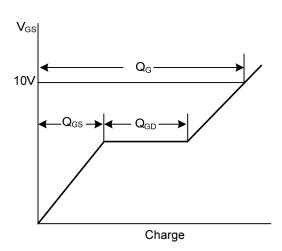
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS		•					
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA				V
Drain-Source Leakage Current			V _{DS} =40V, V _{GS} =0V			20	μΑ
		I _{DSS}	V _{DS} =32V, V _{GS} =0V, T _J =150°C			250	μΑ
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V			+200	nA
	Reverse		V _{GS} =-20V			-200	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Re	sistance	R _{DS(ON)}	V _{GS} =10V, I _D =95A (Note 2)		3.5	4	mΩ
DYNAMIC PARAMETERS						=.	
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		7360		рF
Output Capacitance		Coss			1680		pF
Reverse Transfer Capacitance		C _{RSS}			240		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	-1 -054 \/ -32\/ \/ -40\/		160	200	nC
Gate to Source Charge		Q_{GS}	I _D =95A, V _{DS} =32V, V _{GS} =10V (Note 2)		35		nC
Gate to Drain Charge		Q_GD			42	60	nC
Turn-ON Delay Time		t _{D(ON)}			17		ns
Rise Time		t _R	V_{DD} =20V, I_{D} =95A, R_{G} =2.5 Ω ,		140		ns
Turn-OFF Delay Time		t _{D(OFF)}	R _D =0.21Ω (Note 2)		72		ns
Fall-Time		t _F			26		ns
SOURCE- DRAIN DIODE RATIF	NGS AND	CHARACTE	RISTICS				
Maximum Body-Diode Continuou	us Current	Is	(Note 3)			162	Α
Maximum Body-Diode Pulsed Cu	urrent	I _{SM}	(Note 1)			650	Α
Drain-Source Diode Forward Vol	tage	V_{SD}	I _S =95A, V _{GS} =0V, T _J =25°C (Note 2)			1.3	٧

Notes: 1. Repetitive rating: pulse width limited by maximum junction temperature

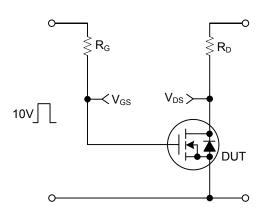
- 2. Pulse width≤300µs, Duty cycle≤2%
- 3. Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A

■ TEST CIRCUITS AND WAVEFORMS

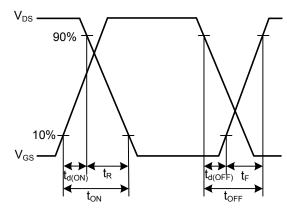




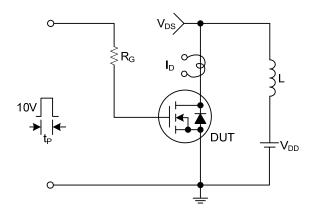
Gate Charge Waveforms



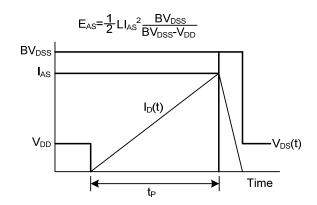
Resistive Switching Test Circuit



Resistive Switching Waveforms

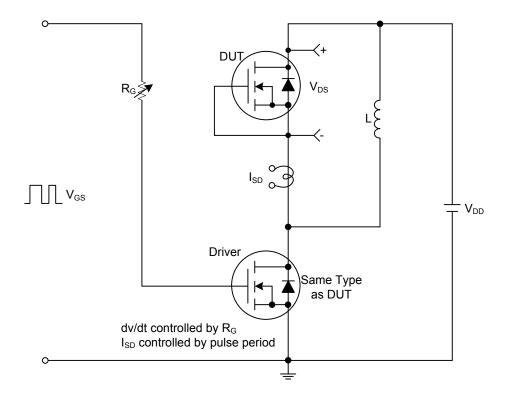


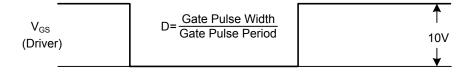
Unclamped Inductive Switching Test Circuit

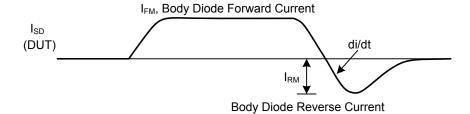


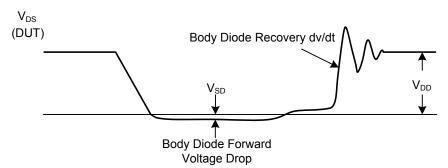
Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)









Peak Diode Recovery dv/dt Test Circuit and Waveforms

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